
2SJ130(L), 2SJ130(S)

Silicon P-Channel MOS FET

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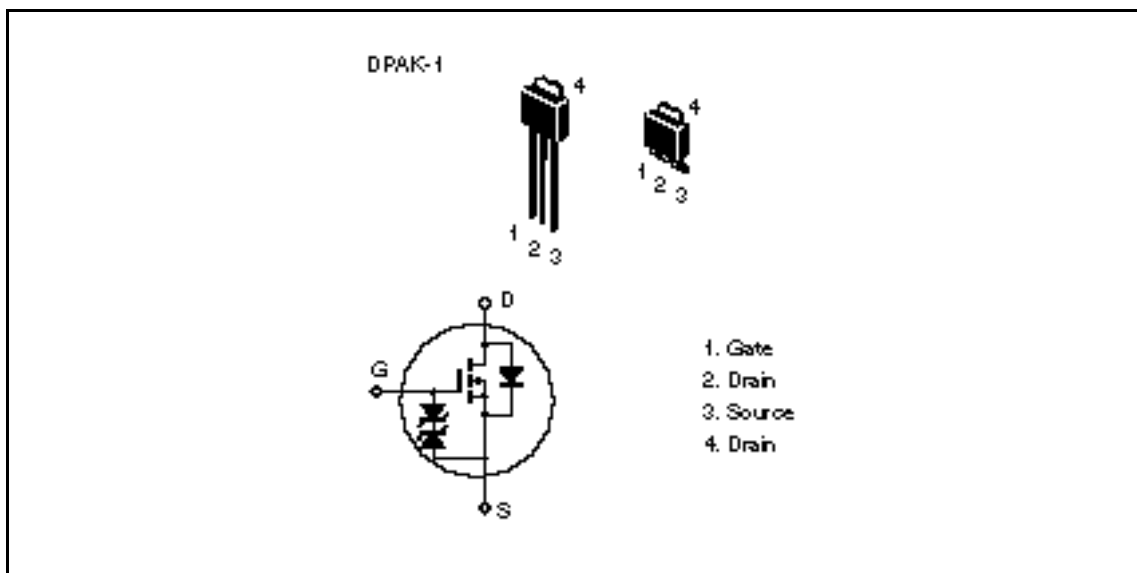
Application

High speed power switching

Features

- Σ Low on-resistance
- Σ High speed switching
- Σ Low drive current
- Σ No secondary breakdown
- Σ Suitable for switching regulator, DC-DC converter and ultrasonic power oscillators

Outline



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Absolute Maximum Ratings (Ta = 25°C)

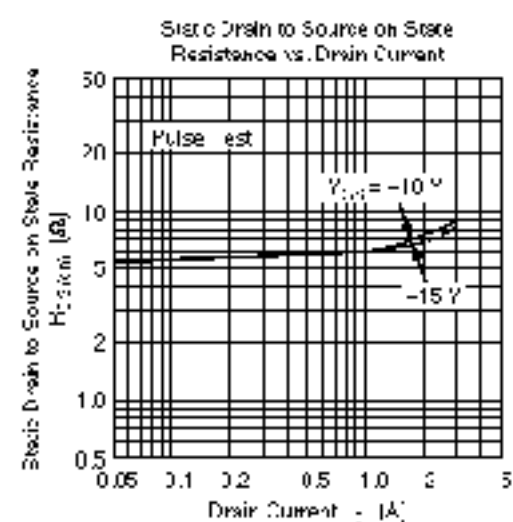
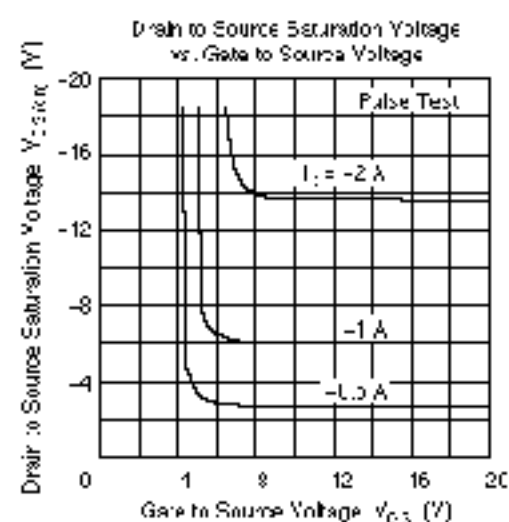
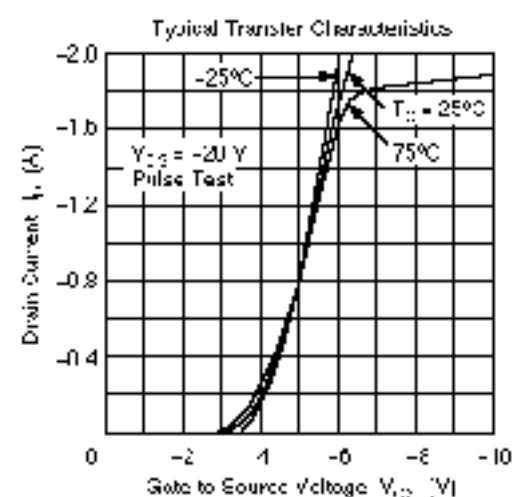
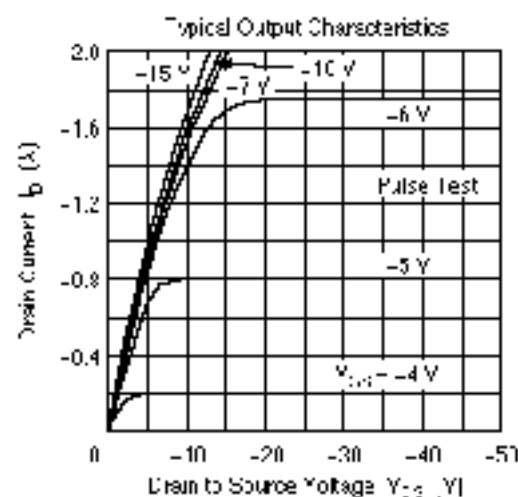
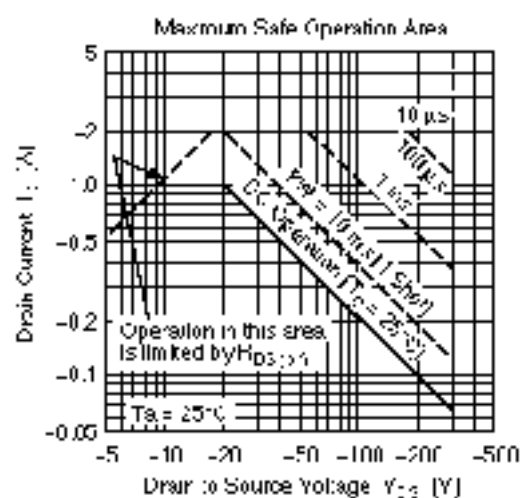
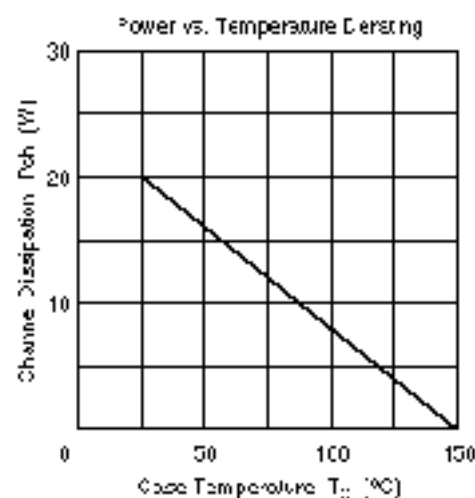
Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	-300	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	-1	A
Drain peak current	$I_{D(pulse)}$	-2	A
Body to drain diode reverse drain current	I_{DR}	-1	A
Channel dissipation	Pch*1	20	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. Value at $T_C = 25^\circ\text{C}$

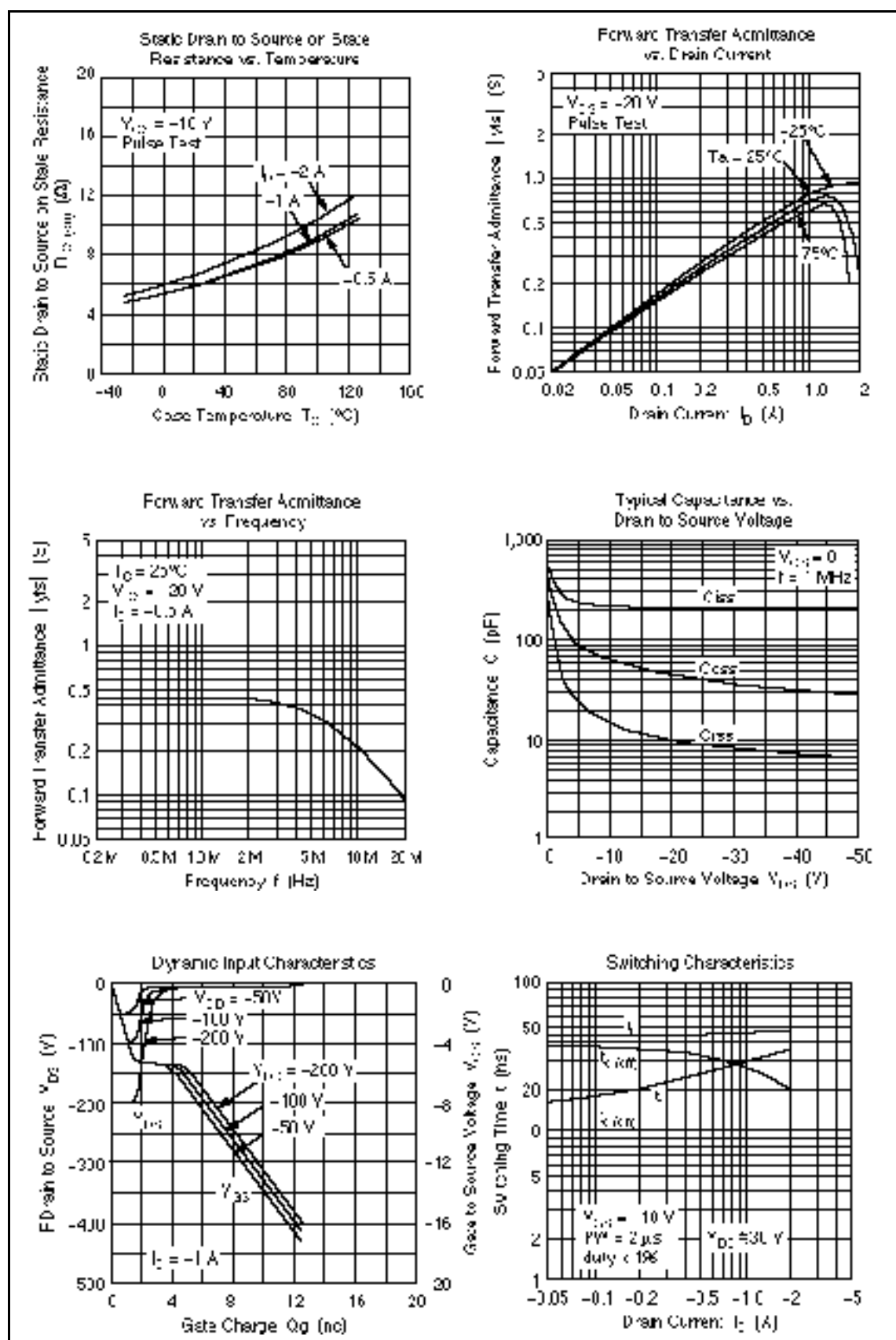
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-300	—	—	V	$I_D = -10\text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100\text{ }\mu\text{A}$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 16\text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-100	μA	$V_{DS} = -240\text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-2.0	—	-4.0	V	$I_D = -1\text{ mA}$, $V_{DS} = -10\text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	6.0	8.5	W	$I_D = -0.5\text{ A}$, $V_{GS} = -10\text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	0.25	0.4	—	S	$I_D = -0.5\text{ A}$, $V_{DS} = -20\text{ V}^{*1}$
Input capacitance	Ciss	—	235	—	pF	$V_{DS} = -10\text{ V}$, $V_{GS} = 0$, $f = 1\text{ MHz}$
Output capacitance	Coss	—	65	—	pF	
Reverse transfer capacitance	Crss	—	16	—	pF	
Turn-on delay time	$t_{d(on)}$	—	10	—	ns	$I_D = -0.5\text{ A}$, $V_{GS} = -10\text{ V}$, $R_L = 60\text{ }\Omega$
Rise time	t_r	—	25	—	ns	
Turn-off delay time	$t_{d(off)}$	—	35	—	ns	
Fall time	t_f	—	45	—	ns	
Body to drain diode forward voltage	V_{DF}	—	-0.9	—	V	$I_F = -1\text{ A}$, $V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	200	—	ns	$I_F = -1\text{ A}$, $V_{GS} = 0$, $di_F/dt = 50\text{ A}/\mu\text{s}$

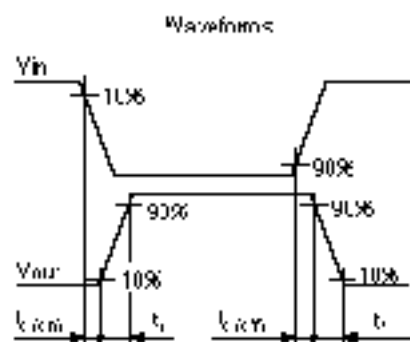
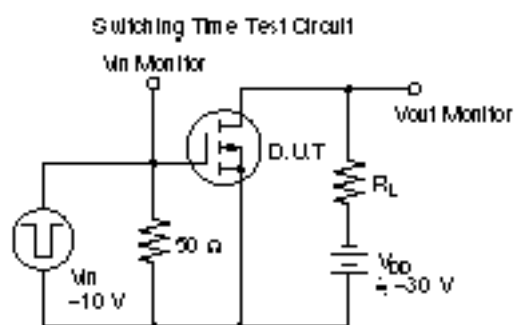
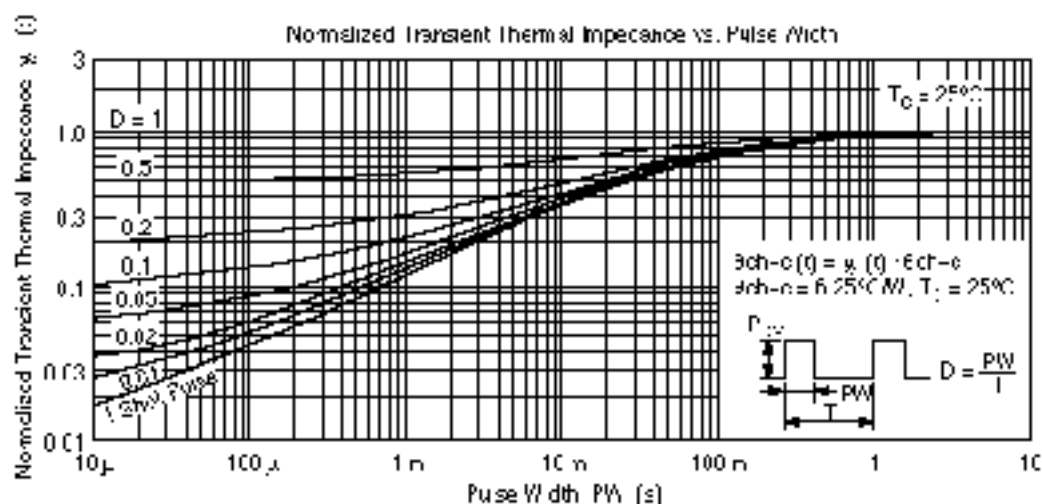
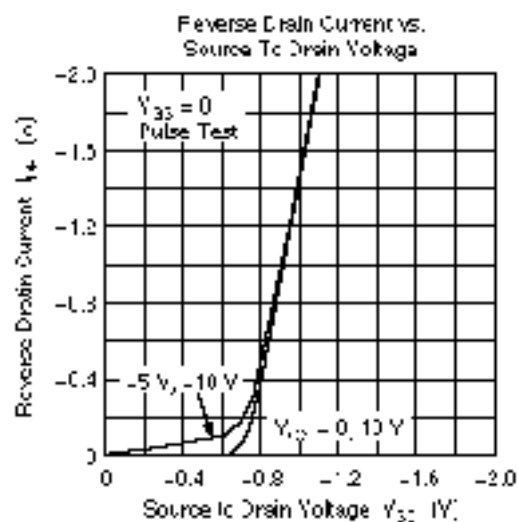
Note: 1. Pulse test



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